

**isc Silicon NPN Power Transistor**

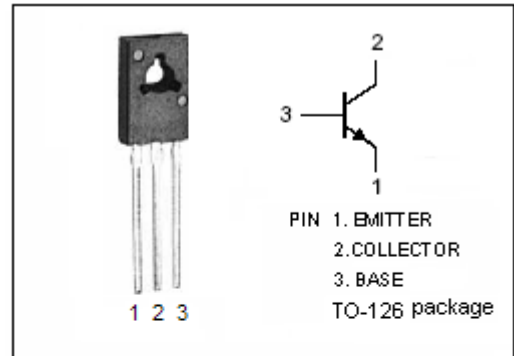
**2SC2481**

**DESCRIPTION**

- Collector-Emitter Breakdown Voltage-  
:  $V_{(BR)CEO} = 150V(\text{Min})$
- High Current Capability
- High Collector Power Dissipation
- Complement to Type 2SA1021

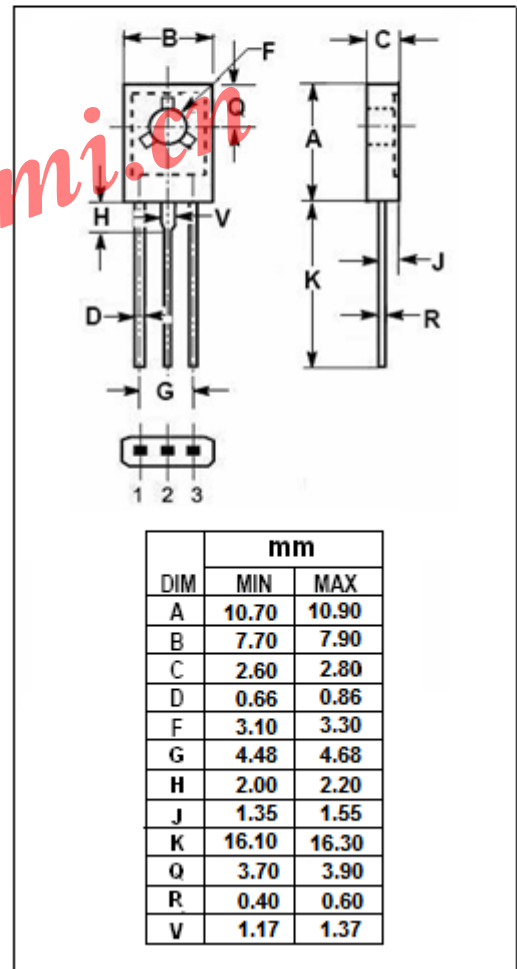
**APPLICATIONS**

- Color TV vertical deflection output applications.
- Color TV class B sound output applications.



**ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	150	V
$V_{CEO}$	Collector-Emitter Voltage	150	V
$V_{EBO}$	Emitter-Base Voltage	6	V
$I_C$	Collector Current-Continuous	1.5	A
$I_B$	Base Current-Continuous	1.0	A
$P_C$	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	20	W
	Collector Power Dissipation @ $T_a=25^\circ\text{C}$	1.2	
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-55~150	$^\circ\text{C}$



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**ELECTRICAL CHARACTERISTICS**

$T_C=25^{\circ}\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C= 10\text{mA}; I_B= 0$	150			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C= 0.5\text{A}; I_B= 50\text{mA}$			1.5	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C= 5\text{mA}; V_{CE}= 5\text{V}$			0.8	V
$I_{CBO}$	Collector Cutoff Current	$V_{CB}= 150\text{V}; I_E= 0$			1.0	$\mu\text{A}$
$I_{EBO}$	Emitter Cutoff Current	$V_{EB}= 6\text{V}; I_C= 0$			1.0	$\mu\text{A}$
$h_{FE}$	DC Current Gain	$I_C= 0.2\text{A}; V_{CE}= 5\text{V}$	60		320	
$f_T$	Current-Gain—Bandwidth Product	$I_C= 0.2\text{A}; V_{CE}= 5\text{V}$	20	100		MHz
$C_{OB}$	Output Capacitance	$I_E= 0; V_{CB}= 10\text{V}, f_{test}= 1\text{MHz}$		13		pF

◆  **$h_{FE}$  Classifications**

R	O	Y
60-120	100-200	160-320